

AMENDMENT TO THE CLAIMS

The following claim listing replaces all prior listings and versions of the claims:

LISTING OF CLAIMS

1-17. (Cancelled)

18. (Currently Amended) An electret comprising:

a charged silicon oxide film;

a first insulating film formed to cover upper and side surfaces of the silicon oxide film;

and

a second insulating film formed to cover a lower surface of the silicon oxide film,

wherein

at least one of the first insulating film and the second insulating film is formed to be in contact with at least one of the upper, side, and lower surfaces of the silicon oxide film.

19. (Previously presented) The electret of claim 18, wherein each of the first and second insulating films is a silicon nitride film.

20. (Previously presented) The electret of claim 18, wherein the silicon oxide film has been charged by a plasma discharge or a corona discharge.

21. (Currently Amended) An electret condenser comprising:

a fixed film having a first electrode; and

a vibrating film disposed with an air gap interposed between itself and the fixed film,

wherein

the vibrating film has a multilayer structure composed of a charged silicon oxide film, a second electrode, a first insulating film, and a second insulating film,

the silicon oxide film is disposed between the first and second electrodes,

upper and side surfaces of the silicon oxide film are covered with the first insulating film,

[[and]]

a lower surface of the silicon oxide film is covered with the second insulating film, and

at least one of the first insulating film and the second insulating film is formed to be in contact with at least one of the upper, side, and lower surfaces of the silicon oxide film.

22. (Previously presented) The electret condenser of claim 21, wherein the lower surface of the silicon oxide film is covered with the second insulating film with the second electrode interposed therebetween.

23. (Previously presented) The electret condenser of claim 21, wherein the vibrating film is formed with a plurality of through holes each reaching the air gap and

a surface of the silicon oxide film which forms each of respective inner wall surfaces of the plurality of through holes is covered with the first insulating film.

24. (Previously presented) The electret condenser of claim 21, wherein each of the first and second insulating films is a silicon nitride film.

25. (Previously presented) The electret condenser of claim 21, wherein each of the first and second electrodes is made of aluminum, an aluminum alloy, silicon, polysilicon, gold, or a refractory metal.

26. (Previously presented) The electret condenser of claim 21, wherein an area of the second electrode is smaller than an area of the silicon oxide film.

27. (Previously presented) The electret condenser of claim 21, wherein the silicon oxide film has been charged by a plasma discharge or a corona discharge.

28. (Currently Amended) An electret condenser comprising:
a semiconductor substrate having a region removed to leave a peripheral portion thereof;
and
a vibrating film formed on the semiconductor substrate to cover the region, wherein
the vibrating film has a multilayer structure composed of a charged silicon oxide film, an
electrode film, a first insulating film, and a second insulating film, [[and]]
upper and side surfaces of the silicon oxide film are covered with the first insulating film
[[and]]
a lower surface of the silicon oxide film is covered with the second insulating film, and
at least one of the first insulating film and the second insulating film is formed to be in
contact with at least one of the upper, side, and lower surfaces of the silicon oxide film.

29. (Previously presented) The electret condenser of claim 28, wherein

the lower surface of the silicon oxide film is covered with the second insulating film with the electrode film interposed therebetween.

30. (Previously presented) The electret condenser of claim 28, wherein the electrode film is disposed between the semiconductor substrate and the silicon oxide film.

31. (Previously presented) The electret condenser of claim 28, wherein each of the first and second insulating films is a silicon nitride film.

32. (Previously presented) The electret condenser of claim 28, wherein the electrode film is formed inside the region in non-overlapping relation with the semiconductor substrate.

33. (New) The electret of claim 18, wherein the first insulating film is formed to be in contact with the upper and side surfaces of the silicon oxide film.

34. (New) The electret of claim 33, wherein the second insulating film is formed to be in contact with the lower surface of the silicon oxide film.

35. (New) The electret of claim 18, wherein the second insulating film is formed to be in contact with the lower surface of the silicon oxide film.

36. (New) The electret condenser of claim 21, wherein the first insulating film is formed to be in contact with the upper and side surfaces of the silicon oxide film.

37. (New) The electret condenser of claim 36, wherein the second insulating film is formed to be in contact with the lower surface of the silicon oxide film.

38. (New) The electret condenser of claim 21, wherein the second insulating film is formed to be in contact with the lower surface of the silicon oxide film.

39. (New) The electret condenser of claim 28, wherein the first insulating film is formed to be in contact with the upper and side surfaces of the silicon oxide film.

40. (New) The electret condenser of claim 39, wherein the second insulating film is formed to be in contact with the lower surface of the silicon oxide film.

41. (New) The electret condenser of claim 28, wherein the second insulating film is formed to be in contact with the lower surface of the silicon oxide film.

42. (New) An electret comprising:
a charged silicon oxide film;
a first silicon nitride film formed to cover upper and side surfaces of the charged silicon oxide film; and
a second silicon nitride film formed to cover a lower surface of the charged silicon oxide film.

43. (New) The electret of claim 42, wherein the first silicon nitride film is formed to be in contact with the upper and side surfaces of the silicon oxide film.

44. (New) The electret of claim 43, wherein the second silicon nitride film is formed to be in contact with the lower surface of the silicon oxide film.

45. (New) The electret of claim 42, wherein the second silicon nitride film is formed to be in contact with the lower surface of the silicon oxide film.